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(54) Title: SINGLE SOURCE SPUTTERING OF THIOALUMINATE PHOSPHOR FILMS

(57) Abstract: A method of deposition of a phosphor in a single-source sputtering process, in which the phosphor is selected from the group consisting of ternary, quaternary or higher thioaluminate, thiogallate and thioindate phosphors, and composites thereof, synthesized with cations selected from Groups IIA and IIB of the Periodic Table of Elements. The phosphor is of a pre-determined composition of elements. The method comprising sputtering in a hydrogen sulphide atmosphere from a single source composition so as to deposit a composition on a substrate. The composition of the targets of the single source has a relative increase in concentration of elements of the phosphor that have a lower atomic weight compared to other elements in said phosphor. The relative increase is controlled such that deposition of the pre-determined composition is effected on the substrate. Preferred phosphors are barium thioaluminate ($\text{BaAl}_2\text{S}_4\text{:Eu}$), and barium magnesium thioaluminates.

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Single Source Sputtering of Thioaluminate Phosphor Films

5 Field of the Invention

The present invention relates to a single-source sputtering process for depositing controlled composition multi-element thin films for use as electroluminescent phosphors. The present invention also provides a phosphor of high luminosity and an emission color that can
10 be tuned by adjusting the film composition. The process entails the use of a source material in the form of a single dense target that has a composition different from the desired film composition of the phosphor. The concentrations of light chemical elements relative to heavier chemical elements in the target composition of the process is
15 higher than desired in the deposited films.

In embodiments, the present invention relates to improving the luminance and emission spectrum of phosphor materials used for full colour ac electroluminescent displays employing thick film dielectric layers with a high dielectric constant. Aspects of the invention also
20 relate to reducing the cost of equipment used to deposit the phosphor materials onto the dielectric layers.

Background to the Invention

A thick film dielectric structure provides for superior resistance to
25 dielectric breakdown as well as a reduced operating voltage in comparison to thin film electroluminescent (TFEL) displays, as exemplified by U.S. Patent 5,432,015. The thick film dielectric structure when it is deposited on a ceramic substrate tends to withstand higher processing temperatures than TFEL devices, which
30 are typically fabricated on glass substrates. This increased high

temperature tolerance facilitates annealing of phosphor films at higher temperatures to improve their luminosity. However, even with this enhancement, thick film electroluminescent displays have not achieved the phosphor luminance and colour coordinates needed to be fully competitive with cathode ray tube (CRT) displays, particularly with recent trends in CRT specifications to higher luminance and higher colour temperature. Some improvement may also be realized by increasing the operating voltage of the displays, but this increases the power consumption of the displays and decreases the reliability and increases the cost of driving electronics for the displays.

A high luminosity full colour electroluminescent display requires that the thin film phosphor materials used for the red, green and blue sub-pixels be patterned so that the emission spectrum for each colour of pixel is tailored to minimize the attenuation resulting from the use of optical filters that are needed to achieve the required colour coordinates for each sub-pixel. For relatively low-resolution displays, the required patterning can be achieved by depositing the phosphor materials through a shadow mask. For high-resolution displays, however, the shadow mask technique does not provide adequate accuracy, and photolithographic methods must be employed. Photolithographic techniques, as exemplified in published PCT patent application WO 00/70917 of Wu et al., require the deposition of photoresist films and the etching or lift-off of portions of the phosphor film to provide the required pattern. Deposition and removal of photoresist films and etching and/or lift-off of phosphor films typically requires the use of solvent solutions that contain water or other protic solvents. These solutions may degrade the properties of phosphor materials, such as strontium sulphide that are subject to hydrolysis.

Traditionally, cerium-activated strontium sulphides for blue and manganese-activated zinc sulphides for red and green have been the

phosphor materials of choice for full colour electroluminescent displays. The optical emission from these phosphor materials must be passed through an appropriate chromatic filter to achieve the necessary colour coordinates for red, green and blue sub-pixels, resulting in a loss of luminance and energy efficiency. The manganese-activated zinc sulphide phosphor has a relatively high electrical to optical energy conversion efficiency of up to about 10 lumens per watt of input power. The cerium-activated strontium sulphide phosphor has an energy conversion efficiency of 1 lumen per watt, relatively high for blue emission. However, the spectral emission for these phosphors is quite wide, with that for the zinc sulphide-based phosphor material spanning the colour spectrum from green to red and that for the strontium sulphide based material spanning the range from blue to green. This necessitates the use of optical filters. The spectral emission of the cerium-activated strontium sulphide phosphor can be shifted to some degree towards the blue by controlling the deposition conditions and activator concentration, but not to the extent required to eliminate the need for an optical filter.

Alternate blue phosphor materials having narrower emission spectra tuned to provide the colour coordinates required for blue sub-pixel have been evaluated. These include cerium-activated alkaline earth thiogallate compounds. Such blue phosphor materials tend to give good blue colour coordinates, but have relatively poor luminosity and stability. Since the host materials are ternary compounds, it is relatively difficult to control the stoichiometry of the phosphor films.

Europium-activated barium thioaluminate provides excellent blue colour coordinates and higher luminance, but it is also a ternary compound and stoichiometry is difficult to control. Vacuum deposition of phosphor films comprising this material from a single source target using sputtering or electron beam evaporation has not yielded films

with high luminosity. Improved luminance of barium thioaluminate phosphors has been achieved by using a hopping electron beam deposition technique to deposit films from two source pellets. The stoichiometry of the deposited film is controlled using the relative dwell
5 time of the electron beam impinging on each of the two source materials. However, this technique is not readily scalable to facilitate commercial production of large area displays and the process cannot be controlled to compensate for changes in the evaporation rates from the two sources as the deposition proceeds and the source pellets are
10 depleted.

Another approach that has been adopted to improve the stoichiometry of the thioaluminate phosphors is to use more than one source for the deposition, but this approach requires added controls over the relative deposition rates for the different sources. The
15 required relative evaporation rates must be calibrated for each specific piece of deposition equipment and the requirement for multiple sources constrains the design of the deposition equipment, generally adding to the cost of the equipment.

20 Summary of the Invention

A single-source sputtering process for depositing controlled composition multi-element phosphors has now been found.

Accordingly, one aspect of the present invention provides a method of deposition of a phosphor in a single-source sputtering
25 process, said phosphor being selected from the group consisting of ternary, quaternary or higher thioaluminate, thiogallate and thioindate phosphors, and composites thereof, synthesized with cations selected from Groups IIA and IIB of the Periodic Table of Elements, said phosphor having a pre-determined composition of elements and being
30 activated with a rare earth element, said method comprising sputtering

in a hydrogen sulphide atmosphere from a single source composition so as to deposit phosphor on a substrate, the composition of the single source having a relative increase in concentration of elements of said phosphor that have a lower atomic weight compared to other elements
5 in said phosphor, said relative increase being controlled such that deposition of said pre-determined composition is effected on the substrate.

In a preferred embodiment of the method of the present invention, the phosphor is selected from the group consisting of
10 activated barium thioaluminate ($\text{BaAl}_2\text{S}_4:\text{Eu}$) and barium magnesium thioaluminates ($\text{Ba}_a\text{Mg}_{1-a}\text{Al}_2\text{S}_4:\text{Eu}$ with $0 < a < 1$).

In another embodiment, said cations include cations selected from the group consisting of barium, calcium, strontium, magnesium, zinc and cadmium.

15 In a further embodiment, the elements of lower atomic weight are at least one of magnesium and aluminum.

In a still further embodiment, the phosphor is activated with europium or cerium.

In accordance with yet another aspect of the present invention,
20 there is provided a single source sputtering process for depositing a thin-film phosphor composition, the process comprising;

- providing a doped target composition having a higher concentration of elements of lower atomic weight relative to higher atomic weight elements with respect to the deposited thin-film
25 phosphor composition;
- sputtering the doped target composition in a sulfur containing atmosphere such that the thin-film phosphor composition is deposited on a substrate, wherein the deposited thin-film phosphor composition has a lower concentration of elements of lower atomic
30 weight relative to higher atomic weight elements.

In accordance with another aspect of the present invention there is provided electroluminescent device, the device comprising;

- a substrate of a thick film ceramic material comprising a ceramic sheet having a electrically conductive film deposited thereon
5 and a thick film layer deposited on the electrically conductive film;
- a thin-film phosphor composition on the thick film layer, the thin-film phosphor composition made by sputtering a doped target composition having a higher concentration of elements of lower atomic weight relative to higher atomic weight elements with respect to the
10 thin-film phosphor composition in a sulfur containing atmosphere such that a thin-film phosphor composition is deposited having a lower concentration of elements of lower atomic weight relative to higher atomic weight elements; and
- an optically transparent electrically conductive film on the
15 thin-film phosphor composition.

Brief Description of the Drawings

The present invention is illustrated by the embodiments shown in the drawings, in which:

- 20 Figure 1 shows a schematic representation of a cross-section of an electroluminescent element comprising a thick film dielectric layer and a phosphor composition typical of the present invention.

Figure 2 shows a schematic representation of a plan view of a full colour electroluminescent pixel and its constituent sub-pixels.

25

Detailed Description of the Invention

- The present invention relates to a process for depositing multi-element thin films for electroluminescent phosphors with a high luminosity and emission color. The process also provides a sputtering
30 means to deposit ternary and other chemically complex phosphor

materials to achieve the desired stoichiometry, and to obtain high energy efficiency and high luminosity phosphor films.

Phosphor materials that have been successfully deposited to provide high electroluminescence are typically ternary or quaternary compounds, where the ratio of three or four constituent elements must be controlled to close tolerances. If stoichiometry of the compound is not adequately controlled, the phosphor material may show reduced performance and lifetime. In the present invention, stoichiometry control for the sputtering process is effected by adjusting the composition of the sputtering target material to compensate for aspects of the sputtering process that cause the elemental composition of the deposited film to be different from that of the target. Such aspects include differences in sticking coefficients of elements condensing onto the film as well as differential sputtering of elements from the surface of the target. These differences are a function of the specific target materials, the deposited film composition and the substrate material upon which the film is deposited.

It has been found that the target should be relatively rich in light elements, such as magnesium and aluminum, relative to the desired abundance of these elements in the deposited film. For example, to deposit an alkaline earth thioaluminate film with a nominal composition of $Mg_xBa_yAl_zS_w:Eu$, the target composition should have a concentration of magnesium and aluminum that is higher than that specified by the nominal composition.

As exemplified herein, phosphor materials comprising europium activated barium thioaluminate and europium-activated magnesium-barium thioaluminate have been deposited using the method described herein and have shown high luminance and energy efficiency.

The preferred substrate is a thick film ceramic material, which is known in the art. In embodiments, the substrate comprises a ceramic

sheet, typically alumina, upon which an electrically conductive film, typically gold or a silver alloy, is deposited. A thick film layer consisting of a ferroelectric material and typically comprising one or more of lead magnesium niobate titanate, lead zirconate titanate or barium titanate is deposited on the electrically conductive film. The phosphor film is
5 deposited on the thick film layer followed by an optically transparent but electrically conductive film to form the second electrode for the resultant sub-pixel.

Thin film dielectric layers may be deposited on the thick film
10 layer to mediate undesirable chemical and physical interactions between the deposited phosphor film and the thick and other underlying layers. Thin film dielectric layers may also be deposited on top of the phosphor film prior to deposition of the optically transparent and electrically conductive film. Such further thin film dielectric layers
15 may be comprised of alumina silicon oxynitride, yttria, hafnia zinc sulphide, barium tantalate, barium titanate, tantalum oxide, aluminum titanate, strontium titanate and the like.

The present invention is further illustrated by the embodiment shown in Figures 1 and 2. Figure 1 shows a cross-section of an
20 electroluminescent device utilizing a phosphor of the present invention. Figure 2 shows a plan view of the electroluminescent device. The electroluminescent device, generally indicated by 10, has a substrate 12 on which is located row electrode 14. Thick film dielectric 16 has thin film dielectric 18 thereon. Thin film dielectric 18 is shown with
25 three pixel columns, referred to as 20, 22 and 24, located thereon. The pixel columns contain phosphors to provide the three basic colours viz. red, green and blue. Pixel column 20 has red phosphor 26 located in contact with thin film dielectric 18. Another thin film dielectric 28 is located on red phosphor 26, and column electrode 30 is located on thin
30 film dielectric 28. Similarly, pixel column 22 has green phosphor 32 on

thin film dielectric 18, with thin film dielectric 34 and column electrode 36 thereon. Pixel column 24 has blue phosphor 38 on thin film dielectric 18, with thin film dielectric 40 and column electrode 42 thereon.

5 The present invention relates to a method of deposition of ternary, quaternary and higher compounds, including other chemically complex compositions, especially phosphors, to achieve the desired stoichiometry, and high energy efficiency and high luminosity phosphor films. Phosphors in the form of ternary, quaternary or higher
10 compounds may be deposited to provide high electroluminescence. However, the ratio of the three or four, or more, constituent elements must be controlled to close tolerances. Control of stoichiometry is important in achieving optimum performance of the phosphor. In the present invention, such control is facilitated by varying the composition
15 of the source or target composition, the composition being varied by providing a controlled excess of elements that have a lower atomic weight.

Phosphor materials comprising europium-activated barium thioaluminate ($\text{BaAl}_2\text{S}_4:\text{Eu}$) and barium magnesium thioaluminates (Ba_a
20 $\text{Mg}_{1-a}\text{Al}_2\text{S}_4:\text{Eu}$ with $0 < a < 1$) may be deposited using the method described herein and have shown high luminance and energy efficiency. It is believed that the method is also applicable to other ternary, quaternary or higher thioaluminate, thiogallate and thioindate phosphors and composites thereof synthesized with the cation or
25 cations for these compounds selected from Groups IIA and IIB of the Periodic Table of Elements in which the target compositions contains mixtures of elements of different atomic weights. Examples of such cations include barium, calcium, strontium, magnesium, zinc and cadmium.

30 The phosphor compositions may be activated with a variety of

dopants, especially europium and cerium.

The method of the invention is believed to be applicable to any ternary, quaternary or higher composition deposited on a substrate. It will be understood that the various source materials would be selected so that a vapour may be created for condensation on the substrate.

The preferred substrate is a substrate that is opaque in the visible and infrared regions of the electromagnetic spectrum. In particular, the substrate is a thick film dielectric layer on a ceramic substrate.

Examples of such substrates include alumina, and metal ceramic composites.

In preferred embodiments, the phosphors are europium-activated barium thioaluminates, optionally including magnesium as described above, which are believed to be less susceptible to hydrolysis than cerium-activated strontium sulphide, thus rendering them easier to pattern using photolithographic techniques.

The deposition of the composition may be carried out in an atmosphere of H_2S , sulphur or other volatile sulphur bearing compounds that will not contaminate the phosphor film as it is deposited if there is a tendency for the deposited compound to be deficient in sulphur. In particular, the deposition is done in a hydrogen sulphide atmosphere so that sputtered species in the film can react with sulphide derived from the hydrogen sulphide to adequately saturate the deposited film with sulphide and achieve the desired film composition. However, in some instances, it may be possible to operate the method without an atmosphere of H_2S .

The present invention provides a method for depositing controlled composition multi-element thin films for use as electroluminescent phosphors that can be tuned by adjusting the film composition. Phosphors with a high luminosity and emission colour are obtained. The luminosity and emission spectra of

electroluminescent phosphor films may be optimized by controlling and adjusting the elemental composition of the films.

Thus, the present invention provides a method of deposition of ternary, quaternary or higher phosphor compositions, especially onto
5 an opaque substrate. The deposition can be done in any contemporary rf magnetron sputtering system, such as those marketed by Edwards, Ulvac and Leybold, that is fitted with a gas injection and exhaust system capable of handling hydrogen sulphide and has a deposition substrate heating means.

10 Table 1 shows a range for the target compositions and deposition conditions for typical phosphor films made according to the present invention.

TABLE 1

		Phosphor
5	Target Composition (mole ratio relative to BaS)	
	Al ₂ S ₃	1.5 – 2.0.
	BaS	1.0
	MgS	0 – 2.5
10	EuS ⁺	0.02 – 0.07
	Deposition rate (nm/min)	20 – 70
	H ₂ S Partial Pressure (torr)	(1–6) x 10 ⁻⁴
	Ar to H ₂ S flow ratio	1 - 5
15	Substrate Temperature (°C)	150 – 350
	Phosphor Film Thickness (nm)	350 – 650
	Phosphor Annealing Temperature (°C)	650 – 750

20 The performance of phosphors made using the range of
parameters given in Table 1 is shown in Table 2.

TABLE 2

5	Luminance at 60V above threshold and 240 Hz (Cd/m ²)	>150
	CIE x coordinate	<0.14
	CIE y coordinate	<0.12
10	Threshold Voltage (V)	<225

The present invention is illustrated by the following examples.

15

Example I

A europium-doped magnesium barium thioaluminate phosphor film was formed on a thick film substrate and subsequently annealed at a temperature of about 750°C for 10 minutes in nitrogen. The thick film substrate comprised a 5 cm by 5 cm by 0.1 cm thick alumina substrate upon which a gold electrode was deposited. A thick film high dielectric constant dielectric layer was then deposited in accordance with the methods exemplified by WO 00/70917. A thin film dielectric consisting of alumina with a thickness of 100-200 nm was deposited on top of the thick film dielectric and the phosphor was sputtered on top of the alumina layer using the sputtering process of this invention.

The nominal composition of the sputtering target was Mg_{0.67}Ba_{0.33}Al_{1.3}S₃:Eu where the atomic ratio of europium to barium was 0.03 The target, cylindrical in shape and with a diameter of 3

inches and a thickness of 4 mm, was fabricated using powders of magnesium sulphide, barium sulphide, aluminum sulphide and europium sulphide that had been passed through a 100 mesh screen and then mixed in the appropriate ratios. The mixed powder was
5 placed in a die and pressed at 50,000 psi to compact the powder. The pressed compact was then sintered under nitrogen at a temperature of 900 °C for 10 minutes.

Deposition was done in an argon and hydrogen sulphide atmosphere with a hydrogen sulphide partial pressure of 5×10^{-4} torr.
10 The flow ratio of argon to hydrogen sulphide was 1.8. The deposition rate was 59 nanometers per minute onto a substrate at a temperature of 300°C. Following deposition, the phosphor-coated substrate was annealed under a nitrogen atmosphere at 700°C for 10 minutes. Subsequently, a second alumina thin film and an indium tin oxide
15 transparent conductor were deposited to provide a second electrode.

The device fabricated as described above was tested using alternating polarity 36 microsecond wide pulses with a peak voltage of 280 volts and a frequency of 240 Hz. The emission colour was blue. The luminance measured at the voltage of 60 volts above the threshold
20 voltage was 155 to 185 candelas per square metre, the CIE x coordinate was 0.14 and the CIE y coordinate was 0.122 to 0.126. The threshold voltage was 215 to 220 volts.

Example II

25

An electroluminescent device was constructed with a design similar to that in Example I, except that the target had the nominal composition $\text{Mg}_{0.64} \text{Ba}_{0.36} \text{Al}_{1.9} \text{S}_{2.9} : \text{Eu}$, where the atomic ratio of europium to barium was 0.03. The processing conditions were also
30 similar to those for Example I, except that the partial pressure of

15

hydrogen sulphide during phosphor deposition was 3.3×10^{-4} torr, the flow ratio of argon to hydrogen sulphide was 2.7, the phosphor deposition rate was 33 nanometers per minute, the substrate temperature during deposition was 280 °C, the thickness of the deposited phosphor was 650 nanometers and the phosphor annealing temperature was 750 °.

This device was tested using the same pulsed driving waveform as for Example I. The emission colour obtained was also blue. The luminance measured at the voltage of 60 volts above the threshold voltage was 160 candelas per square metre, the CIE x coordinate was 0.14, the CIE y coordinate was 0.10 and the threshold voltage was 220 volts.

Example III

15

An electroluminescent device was constructed with a design similar to that in Example I, except that the nominal target composition had no magnesium, the partial pressure of hydrogen sulphide during phosphor deposition was 3.3×10^{-4} torr, the phosphor deposition rate was 33 nanometers per minute, and the phosphor annealing temperature was 750 °C.

This device was tested using the same pulsed driving waveform as for Example 1. The emission colour was also blue. The luminance measured at a voltage 60 volts above the threshold voltage was 177 candelas per square meter, the CIE x coordinate was 0.136, the CIE y coordinate was 0.102 and the threshold voltage was 224 volts.

Claims:

1. A single source sputtering process for depositing a thin-film phosphor composition, said process comprising;
 - 5 - providing a doped target composition having a higher concentration of elements of lower atomic weight relative to higher atomic weight elements with respect to said deposited thin-film phosphor composition;
 - sputtering said doped target composition in a sulfur containing atmosphere such that said thin-film phosphor composition is deposited on a substrate, wherein said deposited thin-film phosphor composition has a lower concentration of elements of lower atomic weight relative to higher atomic weight elements.
- 10 2. The process of claim 1, wherein said doped target composition comprises ternary, quaternary or higher thioaluminate, thiogallate and thioindates and composites thereof containing cations selected from Groups IIA and IIB of the Periodic Table of Elements.
- 15 3. The process of claim 2, wherein said cations are selected from the group consisting of barium, calcium, strontium, magnesium, zinc and cadmium.
- 20 4. The process of claim 3, wherein said doped target composition is doped with dopant selected from the group consisting of europium and cerium.
- 25 5. The process of claim 4, wherein said doped target composition is selected from the group consisting of $\text{BaAl}_2\text{S}_4:\text{Eu}$ and $\text{Ba}_a\text{Mg}_{1-a}\text{Al}_2\text{S}_4:\text{Eu}$ wherein $0 < a < 1$.
- 30

6. The process of claim 5, wherein said doped target composition has a mole ratio, relative to BaS, of Al_2S_3 in the range of 1.5-2.0 and of MgS in the range of 0-2.5.
- 5 7. The process of claim 6, wherein said doped target composition has a mole ratio, relative to BaS, in the range of 0.02-0.07.
8. The process of claim 1, wherein said sulfur containing
10 atmosphere is H_2S .
9. The process of claim 8, wherein said sputtering is conducted at a rate of about 20-70 nm/minute.
- 15 10. The process of claim 9, wherein said substrate is provided at a temperature of about 150°C-350°C.
11. The process of claim 10, wherein said phosphor composition is further annealed at a temperature of about 650°C-750°C for about 10
20 minutes.
12. The process of claim 11, wherein said deposited phosphor composition has a thickness of about 350nm-650 nm.
- 25 13. The process of claim 12, wherein said substrate is a thick film ceramic material.
14. The process of claim 13, wherein said thick film ceramic material comprises a ceramic sheet having a electrically conductive film

deposited thereon and a thick film layer deposited on said electrically conductive film.

15. The process of claim 14, wherein said ceramic material is
5 selected from the group consisting of a ceramic sheet and a metal ceramic composite.

16. The process of claim 15, wherein said ceramic sheet is alumina.

10 17. The process of claim 16, wherein said electrically conductive thin film is selected from the group consisting of gold and silver alloy.

18. The process of claim 17, wherein said thick film layer comprises ferroelectric material.

15

19. The process of claim 18, wherein said ferroelectric material is selected from the group consisting of lead magnesium niobate titanate, lead zirconate titanate, barium titanate and mixtures thereof.

20 20. The process of claim 19, wherein said thick film ceramic material additionally comprises one or more thin film dielectric layers thereon.

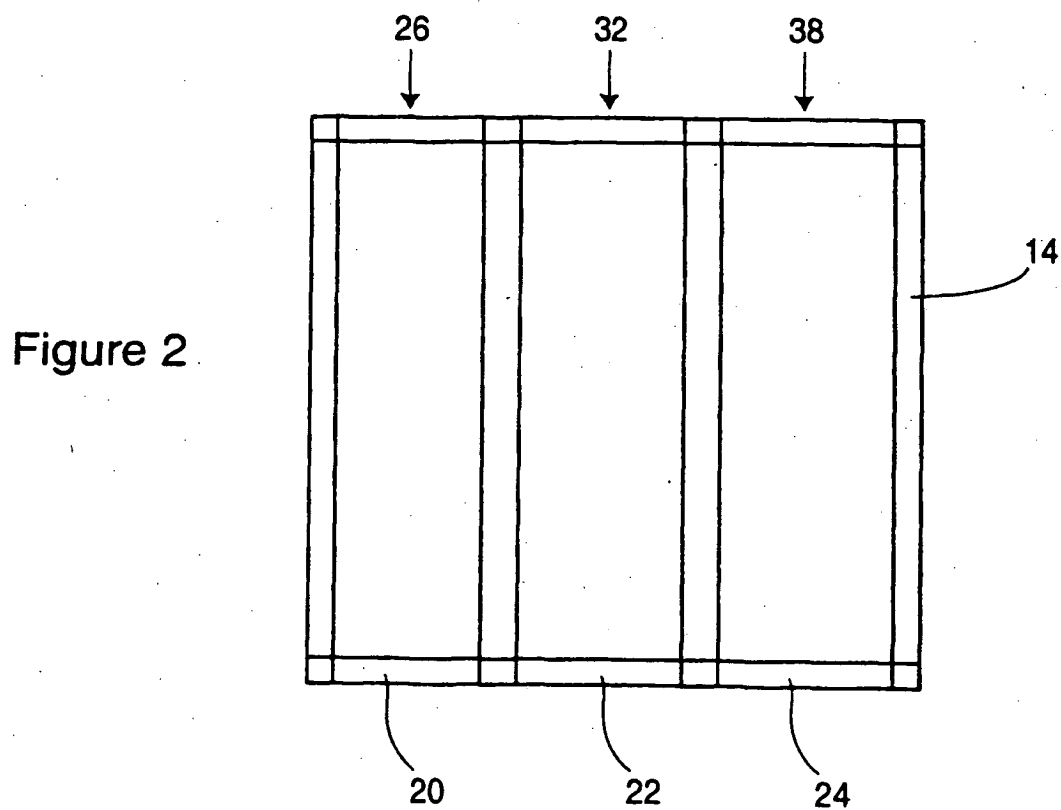
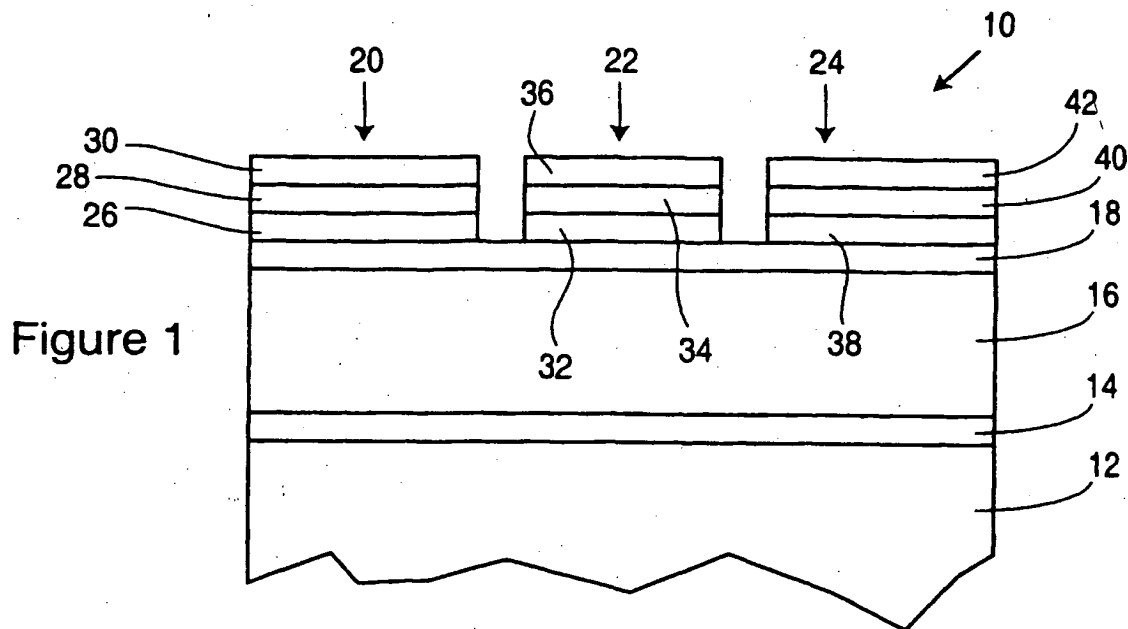
21. The process of claim 20, wherein said thin film dielectric layer comprises a material selected from the group consisting of alumina
25 silicon oxynitride, yttria, hafnia zinc sulfide, barium tantalate, barium titanate, tantalum oxide, aluminum titanate and strontium titanate.

22. The process of claim 21, wherein said process additionally comprises providing a thin film dielectric layer on top of the thin-film
30 phosphor composition.

23. An electroluminescent device, said device comprising;
- a substrate of a thick film ceramic material comprising a ceramic sheet having a electrically conductive film deposited thereon
 - 5 and a thick film layer deposited on said electrically conductive film;
 - a thin-film phosphor composition on said thick film layer, said thin-film phosphor composition made by sputtering a doped target composition having a higher concentration of elements of lower atomic weight relative to higher atomic weight elements with respect to said
 - 10 thin-film phosphor composition in a sulfur containing atmosphere such that a thin-film phosphor composition is deposited having a lower concentration of elements of lower atomic weight relative to higher atomic weight elements; and
 - an optically transparent electrically conductive film on
 - 15 said thin-film phosphor composition.
24. The device of claim 23, wherein said device additionally comprises one or more layers of a thin film dielectric on top of said thin-film phosphor composition.
- 20
25. The device of claim 24, wherein said device additionally comprises one or more layers of a thin film dielectric on top of said thick film layer.
- 25
26. A method of deposition of a phosphor in a single-source sputtering process, said phosphor being selected from the group consisting of ternary, quaternary or higher thioaluminate, thiogallate and thioindate phosphors, and composites thereof, synthesized with cations selected from Groups IIA and IIB of the Periodic Table of
- 30 Elements, said phosphor having a pre-determined composition of

- elements, said method comprising sputtering in a hydrogen sulphide atmosphere from a single source composition so as to deposit a composition on a substrate, the composition of said pellets of the single source having a relative increase in concentration of elements of said
- 5 phosphor that are of greater volatility compared to other elements in said phosphor, said relative increase being controlled such that deposition of said pre-determined composition is effected on the substrate.

1/1



SUBSTITUTE SHEET (RULE 26)

INTERNATIONAL SEARCH REPORT

In oral Application No

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A. CLASSIFICATION OF SUBJECT MATTER
IPC 7 C23C14/06 C23C14/00 C09K11/84

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC 7 C23C C09K

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the International search (name of data base and, where practical, search terms used)

EPO-Internal, PAJ, INSPEC

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 5 309 070 A (SUN SEY-SHING ET AL) 3 May 1994 (1994-05-03) column 3, line 1 - line 15	1-4
Y	column 4, line 35 - line 56	5-8, 23-26
Y	BENALLOUL P ET AL: "IIA-II2-S4 TERNARY COMPOUNDS: NEW HOST MATRICES FOR FULL COLOR THINFILM ELECTROLUMINESCENCE DISPLAYS" APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS, NEW YORK, US, vol. 63, no. 14, 4 October 1993 (1993-10-04), pages 1954-1956, XP000397851 ISSN: 0003-6951 the whole document	5-8, 23-26

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